

Fang-Fang Ren

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127
papers

1,875
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23
h-index

38
g-index

134
ext. papers

2,433
ext. citations

3.8
avg. IF

5.04
L-index

#	Paper	IF	Citations
127	Review of gallium-oxide-based solar-blind ultraviolet photodetectors. <i>Photonics Research</i> , 2019 , 7, 381	6	203
126	Solar-Blind Photodetector with High Avalanche Gains and Bias-Tunable Detecting Functionality Based on Metastable Phase β -GaO/ZnO Isotype Heterostructures. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 36997-37005	9.5	106
125	Controllable electromagnetic transmission based on dual-metallic grating structures composed of subwavelength slits. <i>Applied Physics Letters</i> , 2007 , 91, 111111	3.4	71
124	Electrical instability of amorphous indium-gallium-zinc oxide thin film transistors under monochromatic light illumination. <i>Applied Physics Letters</i> , 2012 , 100, 243505	3.4	66
123	Physical mechanism of extraordinary electromagnetic transmission in dual-metallic grating structures. <i>Physical Review B</i> , 2008 , 78,	3.3	61
122	Giant enhancement of second harmonic generation in a finite photonic crystal with a single defect and dual-localized modes. <i>Physical Review B</i> , 2004 , 70,	3.3	61
121	Split Bull's eye shaped aluminum antenna for plasmon-enhanced nanometer scale germanium photodetector. <i>Nano Letters</i> , 2011 , 11, 1289-93	11.5	60
120	A 1.86-kV double-layered NiO/ β -Ga ₂ O ₃ vertical p-n heterojunction diode. <i>Applied Physics Letters</i> , 2020 , 117, 022104	3.4	58
119	Hybridized surface plasmon polaritons at an interface between a metal and a uniaxial crystal. <i>Applied Physics Letters</i> , 2008 , 92, 141115	3.4	53
118	Enhanced bias stress stability of a-InGaZnO thin film transistors by inserting an ultra-thin interfacial InGaZnO:N layer. <i>Applied Physics Letters</i> , 2013 , 102, 193505	3.4	50
117	Raman-active Fr \ddot{u} lich optical phonon mode in arsenic implanted ZnO. <i>Applied Physics Letters</i> , 2009 , 94, 011913	3.4	45
116	High-Temperature Single Photon Detection Performance of 4H-SiC Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2014 , 26, 1136-1138	2.2	44
115	Gallium oxide-based solar-blind ultraviolet photodetectors. <i>Semiconductor Science and Technology</i> , 2020 , 35, 023001	1.8	40
114	Highly Narrow-Band Polarization-Sensitive Solar-Blind Photodetectors Based on β -GaO Single Crystals. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 7131-7137	9.5	38
113	. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 2276-2281	2.9	33
112	Surface plasmon enhanced responsivity in a waveguided germanium metal-semiconductor-metal photodetector. <i>Applied Physics Letters</i> , 2010 , 97, 091102	3.4	33
111	High Quantum Efficiency GaN-Based p-i-n Ultraviolet Photodetectors Prepared on Patterned Sapphire Substrates. <i>IEEE Photonics Technology Letters</i> , 2013 , 25, 652-654	2.2	32

110	Identification and modulation of electronic band structures of single-phase $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ alloys grown by laser molecular beam epitaxy. <i>Applied Physics Letters</i> , 2018 , 113, 041901	3.4	29
109	Vertically Emitting Indium Phosphide Nanowire Lasers. <i>Nano Letters</i> , 2018 , 18, 3414-3420	11.5	25
108	Band Alignment and Interface Recombination in NiO/ Ga_2O_3 Type-II p-n Heterojunctions. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3341-3347	2.9	24
107	Large-Swing a-IGZO Inverter With a Depletion Load Induced by Laser Annealing. <i>IEEE Electron Device Letters</i> , 2014 , 35, 1034-1036	4.4	24
106	Large-scale fabrication and luminescence properties of GaN nanostructures by a soft UV-curing nanoimprint lithography. <i>Nanotechnology</i> , 2013 , 24, 405303	3.4	24
105	Heteroepitaxial growth of thick Ga_2O_3 film on sapphire (0001) by MIST-CVD technique. <i>Journal of Semiconductors</i> , 2019 , 40, 012804	2.3	24
104	High-Brightness Polarized Green InGaN/GaN Light-Emitting Diode Structure with Al-Coated p-GaN Grating. <i>ACS Photonics</i> , 2016 , 3, 1912-1918	6.3	20
103	On the origin of dislocation generation and annihilation in Ga_2O_3 epilayers on sapphire. <i>Applied Physics Letters</i> , 2019 , 115, 182101	3.4	20
102	Magnesium ion-implantation-based gallium nitride p-i-n photodiode for visible-blind ultraviolet detection. <i>Photonics Research</i> , 2019 , 7, B48	6	20
101	Manipulable and Hybridized, Ultralow-Threshold Lasing in a Plasmonic Laser Using Elliptical InGaN/GaN Nanorods. <i>Advanced Functional Materials</i> , 2017 , 27, 1703198	15.6	19
100	1.37 kV/12 A NiO/ Ga_2O_3 Heterojunction Diode With Nanosecond Reverse Recovery and Rugged Surge-Current Capability. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 12213-12217	7.2	19
99	Realization of p-type gallium nitride by magnesium ion implantation for vertical power devices. <i>Scientific Reports</i> , 2019 , 9, 8796	4.9	18
98	Phase tailoring and wafer-scale uniform hetero-epitaxy of metastable-phased corundum Ga_2O_3 on sapphire. <i>Applied Surface Science</i> , 2020 , 513, 145871	6.7	16
97	High Fill-Factor 4H-SiC Avalanche Photodiodes With Partial Trench Isolation. <i>IEEE Photonics Technology Letters</i> , 2016 , 28, 2526-2528	2.2	16
96	Temperature and gate bias dependence of carrier transport mechanisms in amorphous indiumgalliumzinc oxide thin film transistors. <i>Solid-State Electronics</i> , 2013 , 86, 41-44	1.7	16
95	. <i>IEEE Photonics Technology Letters</i> , 2016 , 28, 1185-1188	2.2	15
94	High Quantum Efficiency Back-Illuminated AlGaN-Based Solar-Blind Ultraviolet p-i-n Photodetectors. <i>Chinese Physics Letters</i> , 2012 , 29, 097302	1.8	14
93	Ga_2O_3 vertical heterojunction barrier Schottky diodes terminated with p-NiO field limiting rings. <i>Applied Physics Letters</i> , 2021 , 118, 202102	3.4	14

92	Transition of photoconductive and photovoltaic operation modes in amorphous Ga ₂ O ₃ -based solar-blind detectors tuned by oxygen vacancies. <i>Chinese Physics B</i> , 2019 , 28, 028501	1.2	13
91	. <i>IEEE Electron Device Letters</i> , 2020 , 1-1	4.4	13
90	Band alignment and band bending at α -Ga ₂ O ₃ /ZnO n-n isotype hetero-interface. <i>Applied Physics Letters</i> , 2019 , 115, 202101	3.4	13
89	In situ heteroepitaxial construction and transport properties of lattice-matched α -Ga ₂ O ₃ / α -Ga ₂ O ₃ p-n heterojunction. <i>Applied Physics Letters</i> , 2021 , 118, 261601	3.4	13
88	High-Voltage Quasi-Vertical GaN Junction Barrier Schottky Diode With Fast Switching Characteristics. <i>IEEE Electron Device Letters</i> , 2021 , 42, 974-977	4.4	13
87	Single nanowire green InGaN/GaN light emitting diodes. <i>Nanotechnology</i> , 2016 , 27, 435205	3.4	13
86	4H-SiC SACM Avalanche Photodiode With Low Breakdown Voltage and High UV Detection Efficiency. <i>IEEE Photonics Journal</i> , 2016 , 8, 1-7	1.8	12
85	Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays. <i>Scientific Reports</i> , 2016 , 6, 23486	4.9	12
84	High-Performance 4H-SiC p-i-n Ultraviolet Photodiode With p Layer Formed by Al Implantation. <i>IEEE Photonics Technology Letters</i> , 2016 , 28, 1189-1192	2.2	11
83	Hybrid Light Emitters and UV Solar-Blind Avalanche Photodiodes based on III-Nitride Semiconductors. <i>Advanced Materials</i> , 2020 , 32, e1904354	2.4	11
82	Analysis of Dark Count Mechanisms of 4H-SiC Ultraviolet Avalanche Photodiodes Working in Geiger Mode. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 4532-4539	2.9	11
81	Extreme absorption enhancement in ZnTe:O/ZnO intermediate band core-shell nanowires by interplay of dielectric resonance and plasmonic bowtie nanoantennas. <i>Scientific Reports</i> , 2017 , 7, 7503	4.9	10
80	High-temperature and reliability performance of 4H-SiC Schottky-barrier photodiodes for UV detection. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 040602	1.3	9
79	Second-order surface-plasmon assisted responsivity enhancement in germanium nano-photodetectors with bull's eye antennas. <i>Optics Express</i> , 2014 , 22, 15949-56	3.3	9
78	Temperature-dependent efficiency droop behaviors of GaN-based green light-emitting diodes. <i>Chinese Physics B</i> , 2013 , 22, 047805	1.2	9
77	Electron-Beam-Driven III-Nitride Plasmonic Nanolasers in the Deep-UV and Visible Region. <i>Small</i> , 2020 , 16, e1906205	1.1	9
76	Bias stress instability involving subgap state transitions in a-IGZO Schottky barrier diodes. <i>Journal Physics D: Applied Physics</i> , 2016 , 49, 395104	3	9
75	A Terahertz Controlled-NOT Gate Based on Asymmetric Rotation of Polarization in Chiral Metamaterials. <i>Advanced Optical Materials</i> , 2017 , 5, 1700108	8.1	8

74	Electromagnetic transmission through one-dimensional gratings with left-handed materials. <i>Physical Review B</i> , 2007 , 75,	3.3	8
73	4H-SiC Ultraviolet Avalanche Photodiodes With Small Gain Slope and Enhanced Fill Factor. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-8	1.8	7
72	Highly Enhanced Inductive Current Sustaining Capability and Avalanche Ruggedness in GaN p-i-n Diodes With Shallow Bevel Termination. <i>IEEE Electron Device Letters</i> , 2020 , 41, 469-472	4.4	7
71	Tailored Emission Properties of ZnTe/ZnTe:O/ZnO Core-Shell Nanowires Coupled with an Al Plasmonic Bowtie Antenna Array. <i>ACS Nano</i> , 2018 , 12, 7327-7334	16.7	7
70	Single Photon Counting Spatial Uniformity of 4H-SiC APD Characterized by SNOM-Based Mapping System. <i>IEEE Photonics Technology Letters</i> , 2017 , 29, 1603-1606	2.2	7
69	4H-SiC Avalanche Photodiode Linear Array Operating in Geiger Mode. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-7	1.8	7
68	Bias-Selective Dual-Operation-Mode Ultraviolet Schottky-Barrier Photodetectors Fabricated on High-Resistivity Homoepitaxial GaN. <i>IEEE Photonics Technology Letters</i> , 2012 , 24, 2203-2205	2.2	7
67	Strong vertical light output from thin silicon rich oxide/SiO ₂ multilayers via in-plane modulation of photonic crystal patterns. <i>Applied Physics Letters</i> , 2008 , 93, 091901	3.4	7
66	High- κ HfO ₂ -Based AlGaIn/GaN MIS-HEMTs With Y ₂ O ₃ Interfacial Layer for High Gate Controllability and Interface Quality. <i>IEEE Journal of the Electron Devices Society</i> , 2020 , 8, 15-19	2.3	7
65	Split Bullseye Antenna for High-Speed Photodetector in the Range of Visible to Mid-Infrared. <i>IEEE Photonics Technology Letters</i> , 2016 , 28, 1177-1180	2.2	7
64	Distinct enhancement of sub-bandgap photoresponse through intermediate band in high dose implanted ZnTe:O alloys. <i>Scientific Reports</i> , 2017 , 7, 44399	4.9	6
63	Spatial Non-Uniform Hot Carrier Luminescence From 4H-SiC p-i-n Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2019 , 31, 447-450	2.2	6
62	Frequency Performance of Ring Oscillators Based on a-IGZO Thin-Film Transistors. <i>Chinese Physics Letters</i> , 2015 , 32, 047302	1.8	6
61	Study on interface characteristics in amorphous indium-gallium-zinc oxide thin-film transistors by using low-frequency noise and temperature dependent mobility measurements. <i>Solid-State Electronics</i> , 2015 , 109, 37-41	1.7	6
60	Investigation of surface-plasmon coupled red light emitting InGaIn/GaN multi-quantum well with Ag nanostructures coated on GaN surface. <i>Journal of Applied Physics</i> , 2015 , 117, 153103	2.5	6
59	Anion Engineering Enhanced Response Speed and Tunable Spectral Responsivity in Gallium-Oxynitrides-Based Ultraviolet Photodetectors. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 808-816	4	6
58	Vertical 4H-SiC n-i-p-n APDs With Partial Trench Isolation. <i>IEEE Photonics Technology Letters</i> , 2018 , 30, 805-808	2.2	6
57	Effect of Very High-Fluence Proton Radiation on 6H-SiC Photoconductive Proton Detectors. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1929-1932	4.4	6

56	Passive Quenching Electronics for Geiger Mode 4H-SiC Avalanche Photodiodes. <i>Chinese Physics Letters</i> , 2015 , 32, 128501	1.8	6
55	Demonstration of an AlGaIn-based solar-blind high-voltage photoconductive switch. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 040601	1.3	6
54	Solar-blind ultraviolet band-pass filter based on metal-dielectric multilayer structures. <i>Chinese Physics B</i> , 2014 , 23, 074201	1.2	6
53	Raman probing of competitive laser heating and local recrystallization effect in ZnO nanocrystals. <i>Optics Express</i> , 2012 , 20, 23281-9	3.3	6
52	Avalanche Ruggedness of GaN p-i-n Diodes Grown on Sapphire Substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1800069	1.6	6
51	Demonstration of Avalanche and Surge Current Robustness in GaN Junction Barrier Schottky Diode With 600-V/10-A Switching Capability. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 12163-12167	7.2	6
50	Bloch surface plasmon enhanced blue emission from InGaIn/GaN light-emitting diode structures with Al-coated GaN nanorods. <i>Nanotechnology</i> , 2015 , 26, 125201	3.4	5
49	High Deep-Ultraviolet Quantum Efficiency GaN PIN Photodetectors with Thin P-GaN Contact Layer. <i>Chinese Physics Letters</i> , 2013 , 30, 017302	1.8	5
48	Second-harmonic generation in photonic crystals with a pair of epsilon-negative and mu-negative defects. <i>Optics Express</i> , 2009 , 17, 6682-7	3.3	5
47	Gate-first process compatible, high-quality in situ SiN _x for surface passivation and gate dielectrics in AlGaIn/GaN MISHEMTs. <i>Journal Physics D: Applied Physics</i> , 2019 , 52, 305105	3	4
46	High-Performance 4H-SiC Schottky Photodiode With Semitransparent Grid-Electrode for EUV Detection. <i>IEEE Photonics Technology Letters</i> , 2020 , 32, 791-794	2.2	4
45	Boosting Hot-Electron Extraction Through Deep Groove Perfect Absorber for Si-Based Photodetector. <i>IEEE Photonics Technology Letters</i> , 2017 , 29, 1884-1887	2.2	4
44	Metal-semiconductor-metal ultraviolet photodetectors directly fabricated on semi-insulating GaN:Fe template grown by hydride vapor phase epitaxy. <i>Sensors and Actuators A: Physical</i> , 2014 , 216, 308-311	3.9	4
43	Low-threshold and high-efficiency optical parametric oscillator using a one-dimensional single-defect photonic crystal with quadratic nonlinearity. <i>Physical Review B</i> , 2006 , 73,	3.3	4
42	A self-powered solar-blind photodetector based on polyaniline/EGa ₂ O ₃ p-n heterojunction. <i>Applied Physics Letters</i> , 2021 , 119, 141601	3.4	4
41	High Performance Quasi-Vertical GaN Junction Barrier Schottky Diode with Zero Reverse Recovery and Rugged Avalanche Capability 2021 ,		4
40	High-voltage photoconductive semiconductor switches fabricated on semi-insulating HVPE GaN:Fe template. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016 , 13, 374-377		4
39	Crosstalk Analysis of SiC Ultraviolet Single Photon Avalanche Photodiode Arrays. <i>IEEE Photonics Journal</i> , 2019 , 11, 1-8	1.8	4

38	Temperature-dependent bias-stress-induced electrical instability of amorphous indium-gallium-zinc-oxide thin-film transistors. <i>Chinese Physics B</i> , 2015 , 24, 077307	1.2	3
37	Polarization-Independent Indium Phosphide Nanowire Photodetectors. <i>Advanced Optical Materials</i> , 2020 , 8, 2000514	8.1	3
36	Investigations of the gate instability characteristics in Schottky/ohmic type p-GaN gate normally-off AlGaN/GaN HEMTs. <i>Applied Physics Express</i> , 2019 , 12, 121005	2.4	3
35	Enhanced Vertical Light Extraction From Ultrathin Amorphous Si ₃ N ₄ Multilayers With Photonic Crystal Patterns. <i>IEEE Photonics Technology Letters</i> , 2009 , 21, 91-93	2.2	3
34	Saturation effect and forward-dominant second-harmonic generation in single-defect photonic crystals with dual localizations. <i>Optics Letters</i> , 2006 , 31, 3327-9	3	3
33	Dual localizations for second-harmonic generations using left-handed materials. <i>Applied Physics Letters</i> , 2005 , 87, 251104	3.4	3
32	Low-threshold ultraviolet stimulated emissions from large-sized single crystalline ZnO transferable membranes. <i>Optics Express</i> , 2018 , 26, 31965-31975	3.3	3
31	1.2 kV/25 A Normally off P-N Junction/AlGaN/GaN HEMTs With Nanosecond Switching Characteristics and Robust Overvoltage Capability. <i>IEEE Transactions on Power Electronics</i> , 2022 , 37, 26-30 ^{7,2}		3
30	Performance improvement of 4H-SiC PIN ultraviolet avalanche photodiodes with different intrinsic layer thicknesses. <i>Chinese Physics B</i> , 2019 , 28, 098503	1.2	2
29	Off-state breakdown and leakage current transport analysis of AlGaN/GaN high electron mobility transistors. <i>Microelectronics Reliability</i> , 2014 , 54, 2406-2409	1.2	2
28	Spectrum broadening of high-efficiency second harmonic generation in cascaded photonic crystal microcavities. <i>Optics Express</i> , 2013 , 21, 756-63	3.3	2
27	Nanometer germanium photodetector with aluminum surface plasmon antenna for enhanced photo-response 2010 ,		2
26	Polarization-independent split bull's eye antennas for infrared nano-photodetectors. <i>Scientific Reports</i> , 2016 , 6, 39106	4.9	2
25	Band Alignment and Enhanced Interfacial Conductivity Manipulated by Polarization in a Surfactant-Mediated Grown $\text{Ga}_2\text{O}_3/\text{In}_2\text{O}_3$ Heterostructure. <i>ACS Applied Electronic Materials</i> , 2021 , 3, 795-803	4	2
24	70- μm -Body Ga ₂ O ₃ Schottky Barrier Diode with 1.48 K/W Thermal Resistance, 59 A Surge Current and 98.9% Conversion Efficiency. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4	2
23	M-Plane Ga_2O_3 Solar-Blind Detector With Record-High Responsivity-Bandwidth Product and High-Temperature Operation Capability. <i>IEEE Electron Device Letters</i> , 2022 , 43, 541-544	4.4	2
22	Unlocking the Single-Domain Heteroepitaxy of Orthorhombic Ga_2O_3 via Phase Engineering. <i>ACS Applied Electronic Materials</i> , 2022 , 4, 461-468	4	2
21	Si-based Multiband Terahertz Antennas 2019 ,		1

20	Investigation and active suppression of self-heating induced degradation in amorphous InGaZnO thin film transistors. <i>Chinese Physics B</i> , 2019 , 28, 017303	1.2	1
19	Effect of a Single Threading Dislocation on Electrical and Single Photon Detection Characteristics of 4H-SiC Ultraviolet Avalanche Photodiodes. <i>Chinese Physics Letters</i> , 2020 , 37, 068502	1.8	1
18	Misfit epitaxial strain manipulated transport properties in cubic In ₂ O ₃ hetero-epilayers. <i>Applied Physics Letters</i> , 2020 , 117, 102104	3.4	1
17	After-Pulse Characterizations of Geiger-Mode 4H-SiC Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2020 , 32, 706-709	2.2	1
16	GaN Schottky Barrier Diodes with High-Resistivity Edge Termination Formed by Boron Implantation. <i>Chinese Physics Letters</i> , 2013 , 30, 057303	1.8	1
15	Majority and Minority Carrier Traps in NiO/AlGaO ₂ /p-n Heterojunction Diode. <i>IEEE Transactions on Electron Devices</i> , 2022 , 1-7	2.9	1
14	Development of p-i-n radiation detectors based on semi-insulating 4H-SiC substrate via dual-face ion implantation. <i>Solid-State Electronics</i> , 2021 , 187, 108196	1.7	1
13	Strain-driven phase manipulation of Al and AlGa ₂ O ₃ by nanoepitaxial lateral overgrowth on embedded In ₂ O ₃ submicron dots. <i>Applied Physics Letters</i> , 2021 , 119, 182102	3.4	1
12	Field-Plated NiO/Ga ₂ O ₃ p-n Heterojunction Power Diodes With High-Temperature Thermal Stability and Near Unity Ideality Factors. <i>IEEE Journal of the Electron Devices Society</i> , 2021 , 1-1	2.3	1
11	Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays		1
10	Property manipulation through pulsed laser annealing in high dose Mg-implanted GaN. <i>Journal of Applied Physics</i> , 2020 , 128, 235704	2.5	1
9	High sensitivity x-ray detectors based on 4H-SiC p-i-n structure with 80 nm thick intrinsic layer. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2021 , 39, 022202	1.3	1
8	Vertical Field-Plated NiO/Ga ₂ O ₃ Heterojunction Power Diodes 2021 ,		1
7	Electrical Instability of Amorphous-Indium-Gallium-Zinc-Oxide Thin-Film Transistors under Ultraviolet Illumination. <i>Chinese Physics Letters</i> , 2016 , 33, 038502	1.8	1
6	Dislocation dynamics in AlGa ₂ O ₃ micropillars from selective-area epitaxy to epitaxial lateral overgrowth. <i>Applied Physics Letters</i> , 2022 , 120, 121601	3.4	1
5	Over 1.8 GW/cm ² beveled-mesa NiO/AlGa ₂ O ₃ heterojunction diode with 800 V/10 A nanosecond switching capability. <i>Applied Physics Letters</i> , 2021 , 119, 262103	3.4	1
4	Vacuum Violet Photo-Response of AlGaN-Based Metal-Semiconductor-Metal Photodetectors. <i>Chinese Physics Letters</i> , 2013 , 30, 117301	1.8	0
3	1000-W Resistive Energy Dissipating Capability Against Inductive Transients Demonstrated in Non-Avalanche AlGaN/GaN Schottky Diode. <i>IEEE Electron Device Letters</i> , 2021 , 42, 1743-1746	4.4	0

- 2 4H-SiC \bar{n} -i-p extreme ultraviolet detector with gradient doping-induced surface junction. *IEEE Electron Device Letters*, **2022**, 1-1 4.4 ○
- 1 The Effect of Oxygen Partial Pressure during Active Layer Deposition on Bias Stability of a-InGaZnO TFTs. *Chinese Physics Letters*, **2015**, 32, 077303 1.8